N-Channel 30V (D-S) MOSFET

Product Summary		
V_{DS}(V)	$R_{DS(on)}$ (mΩ) (Max.)	I_D (A)
30	24 at V_{GS} = 10 V	12
	30 at V_{GS} = 4.5 V	12

Features

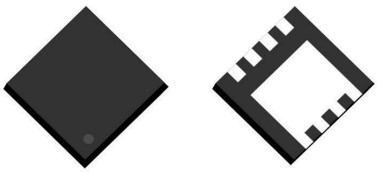
- Very Low RDS(on) at 4.5V Vgs
- Low Gate Charge
- High Current Capability
- 100% Rg and UIS Tested
- RoHS and Halogen-Free Compliant

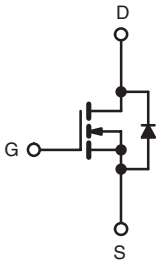
Applications

- Notebook PC
- System Power
- Load Switch

Pin Configuration

DFN3x3





N-Channel MOSFET

Packing Information

Device	Marking	Reel Size	Tape Width	Quantity
EC4330	ECX .XXX	13”	12mm	3000pcs

Absolute Maximum Ratings

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[D]	T_C=25℃	I_D	12	A
	T_C=70°C		12	
Pulsed Drain Current [C]		I_{DM}	30	
Continuous Drain Current	T_A=25℃	I_{DSM}	8.7	A
	T_A=70℃		7	
Avalanche Current [C]		I_{AS}, I_{AR}	5	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	1.25	mJ
Power Dissipation [B]	T_C=25℃	P_D	15.6	W
	T_C=70°C		10	
Power Dissipation [A]	T_A=25℃	P_{DSM}	3.2	W
	T_A=70℃		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Data

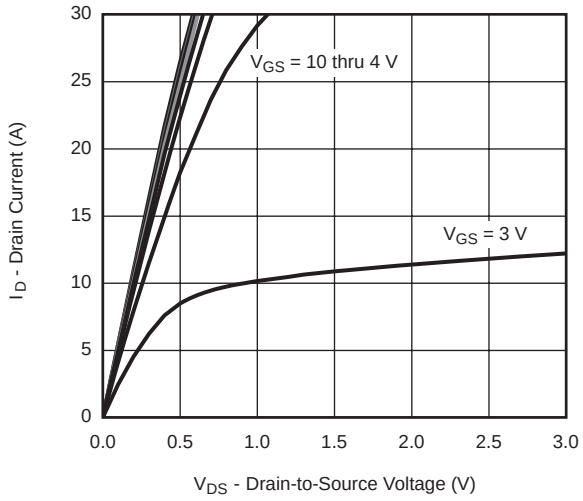
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	32	39	℃/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	6.5	8	℃/W

Electrical Characteristics (T_J=25℃ Unless Otherwise Specified)

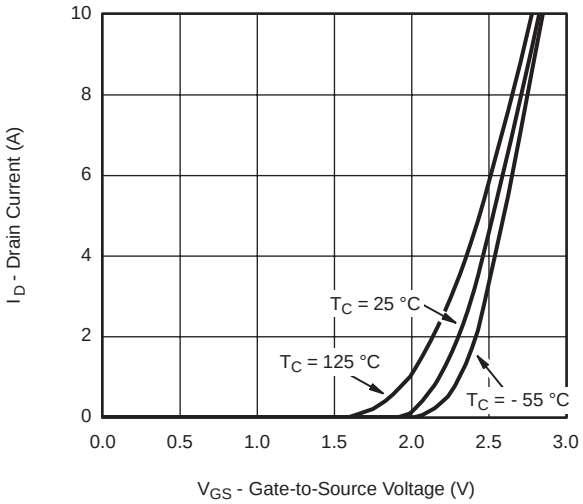
Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	μA
		T_J=55℃			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA	1.0			2.5
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}≥ 5V	20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=7.8A		0.020	0.024	Ω
		V_{GS}=4.5V, I_D=7.0A		0.024	0.030	Ω
g_{FS}	Forward Transconductance	V_{DS}=10V, I_D=7.8A		17		S
V_{SD}	Diode Forward Voltage	I_S=6.3A,V_{GS}=0V		0.8	1.2	V
I_S	Maximum Body-Diode Continuous Current[D]	T_C = 25 °C			4.2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0V, f=1MHz		435		pF
C_{oss}	Output Capacitance			95		
C_{rss}	Reverse Transfer Capacitance			42		
R_g	Gate resistance	f=1MHz	1.5	3.2	4.5	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{DS}=15V, V_{GS} = 10 V, I_D =7.8 A		8	12	nC
Q_g(4.5V)	Total Gate Charge	V_{DS}=15V, V_{GS} = 4.5V, I_D =7.8 A		3.8	6	
Q_{gs}	Gate Source Charge			1.4		
Q_{gd}	Gate Drain Charge			1.1		nC
$t_{D(on)}$	Turn-On DelayTime	V_{DD} = 15 V, R_L = 2.4 Ω I_D ≅6.3 A, V_{GEN} = 4.5V, R_g=1Ω		15	25	ns
t_r	Turn-On Rise Time			12	20	ns
$t_{D(off)}$	Turn-Off DelayTime			13	20	ns
t_f	Turn-Off Fall Time			10	15	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F = 6.3 A, dI/dt = 100 A/μs, T_J = 25 °C		7	12	ns
Q_{rr}	Body Diode Reverse Recovery Charge			9		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150° C may be used if the PCB allows it.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
D. The maximum current rating is package limited.

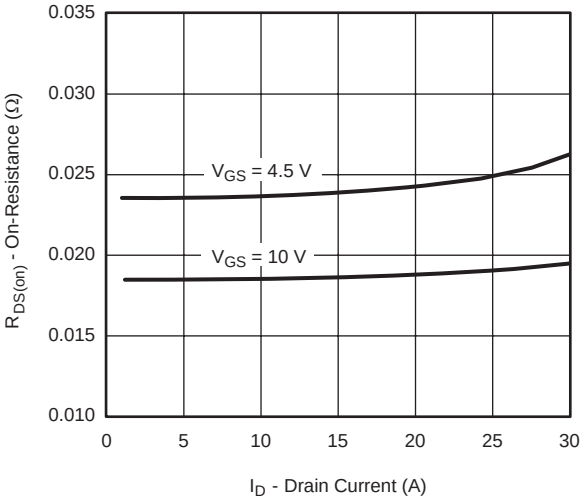
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



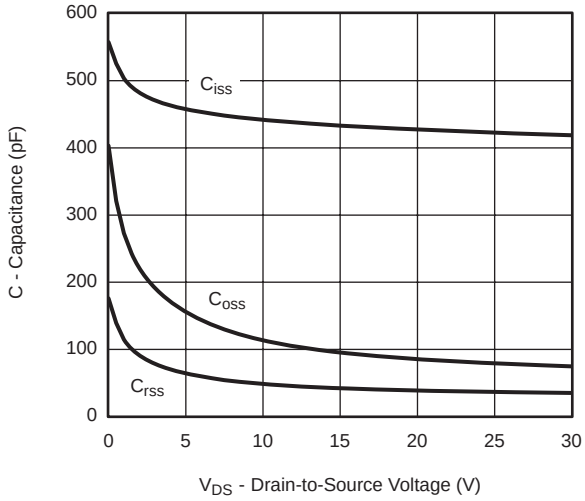
Output Characteristics



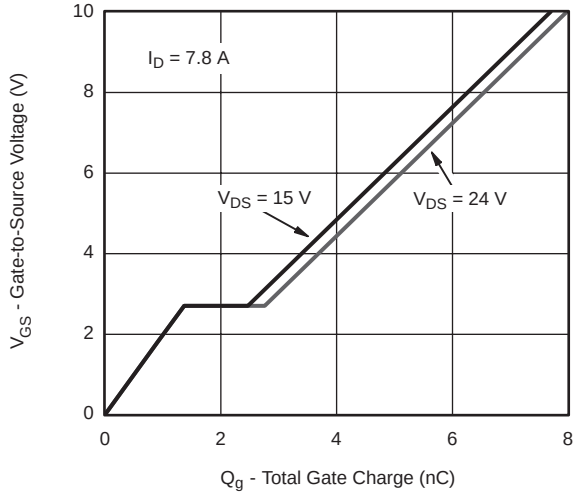
Transfer Characteristics



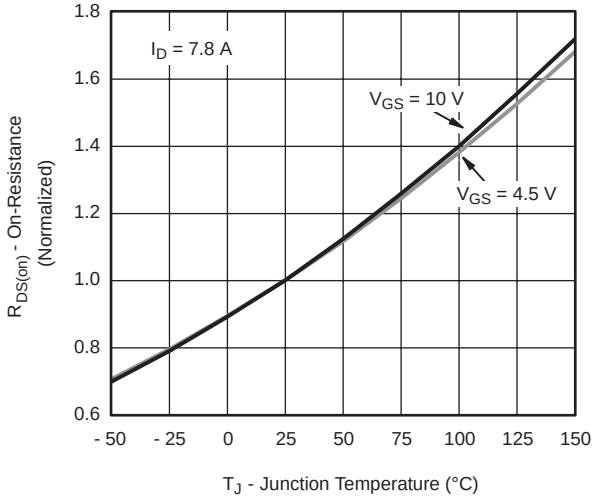
On-Resistance vs. Drain Current



Capacitance

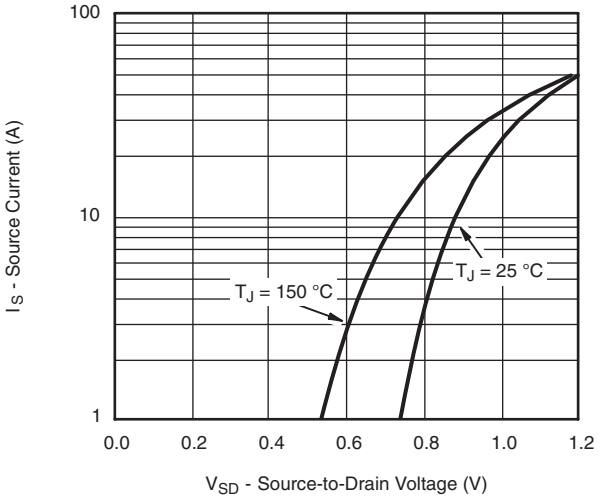


Gate Charge

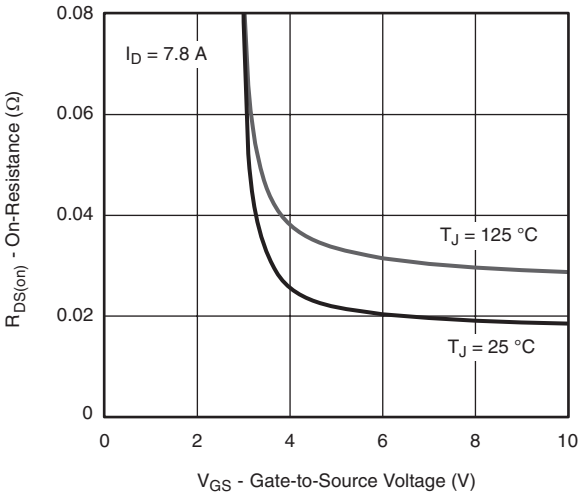


On-Resistance vs. Junction Temperature

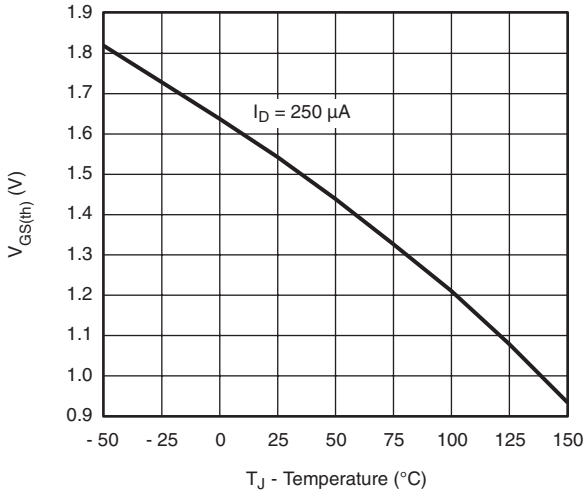
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



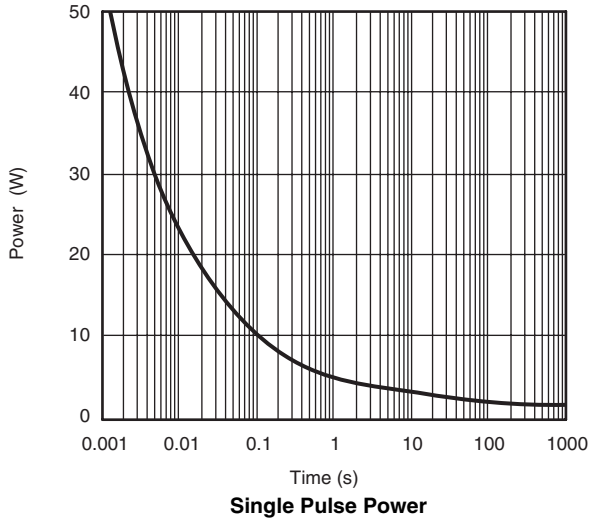
Source-Drain Diode Forward Voltage



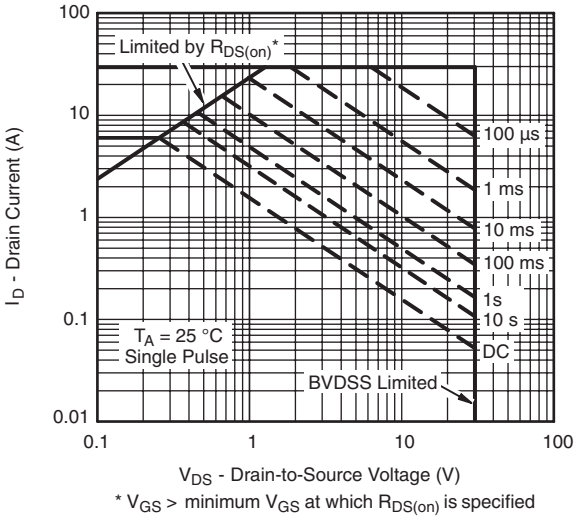
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



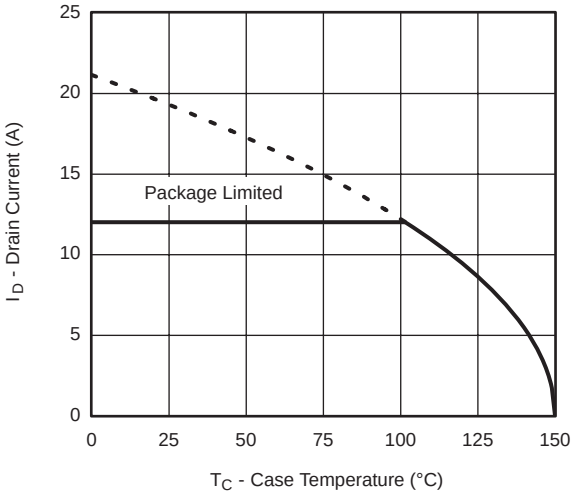
Single Pulse Power



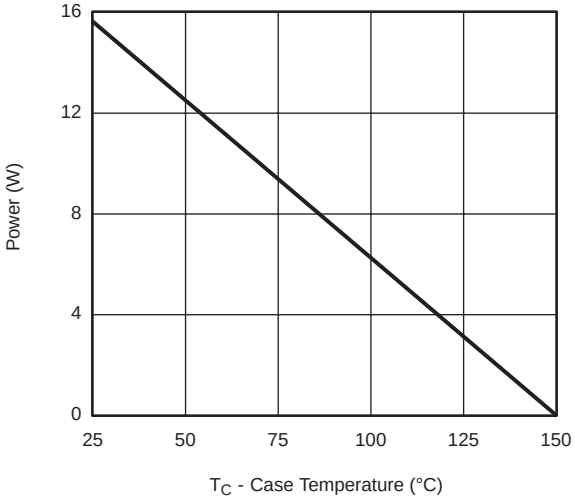
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



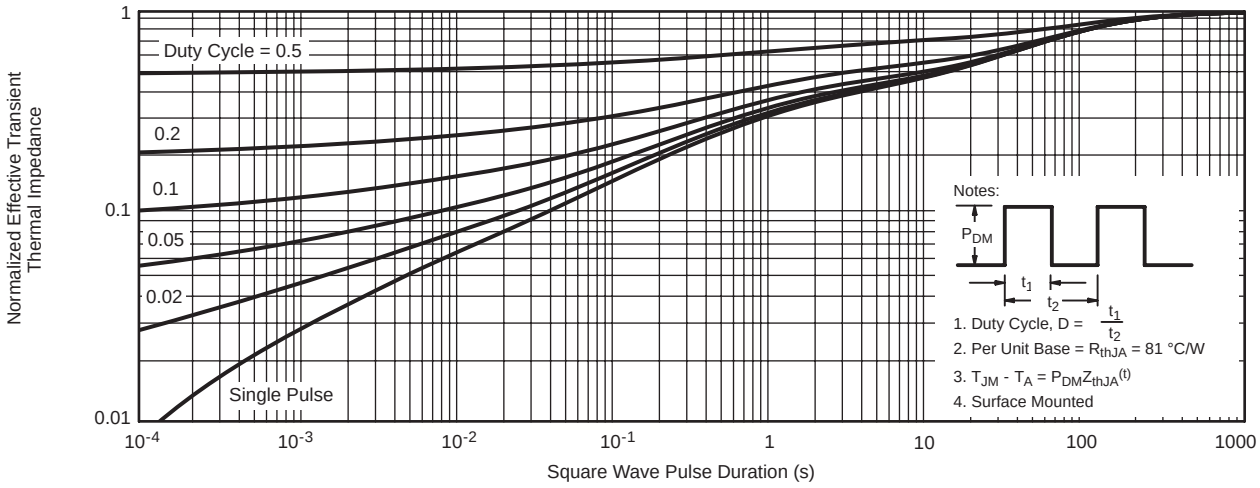
Current Derating*



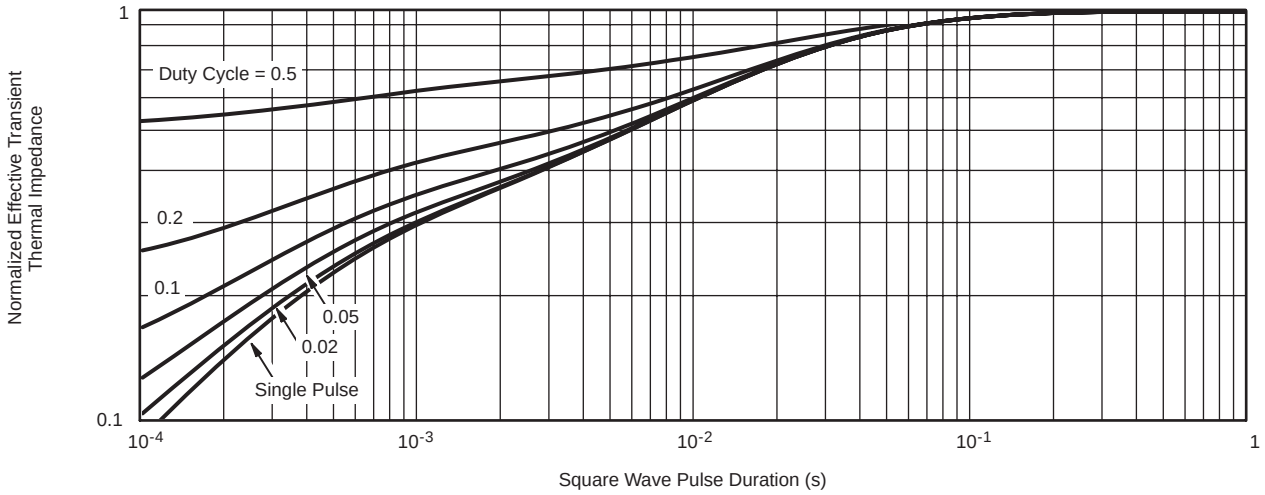
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

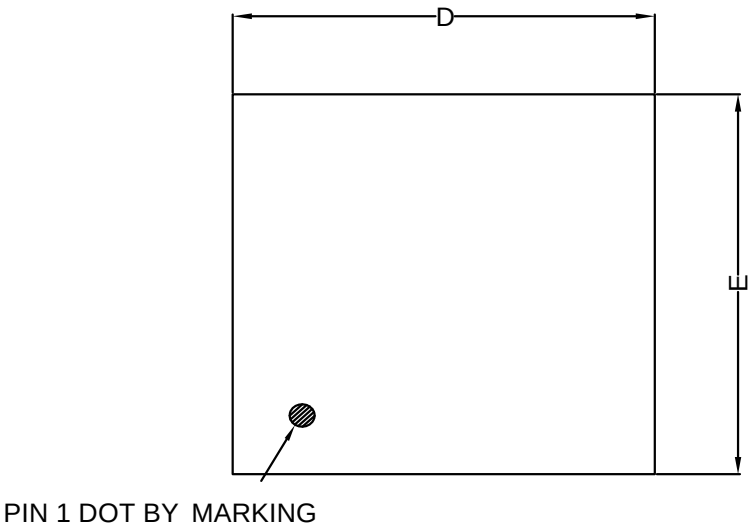


Normalized Thermal Transient Impedance, Junction-to-Ambient

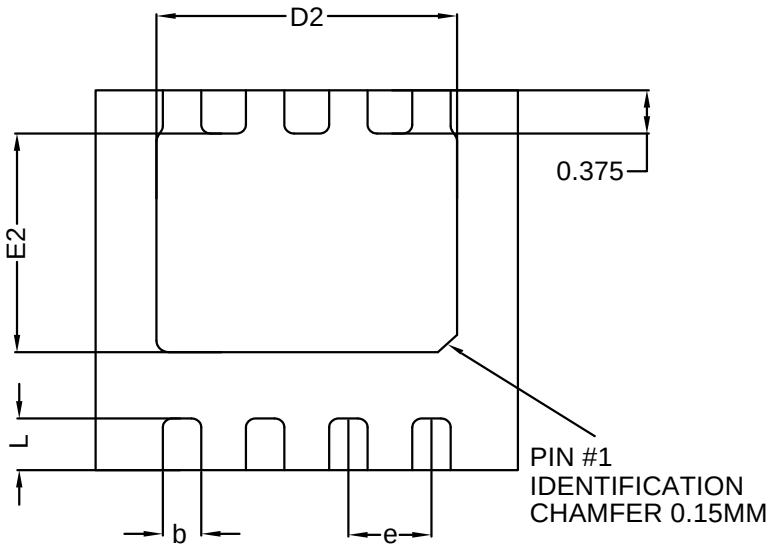


Normalized Thermal Transient Impedance, Junction-to-Case

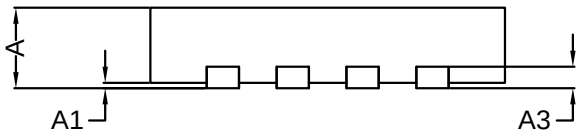
DFN3x3 Package Information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

COMMON DIMENSIONS(MM)			
PKG.	UT:ULTRA THIN		
REF.	MIN.	NOM.	MAX
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF.		
D	3.25	3.30	3.35
E	3.25	3.30	3.35
D2	2.30	2.35	2.40
E2	1.85	1.90	1.95
b	0.25	0.30	0.35
L	0.35	0.45	0.55
e	0.65 BSC		